



HALO-99-006BB



February 9, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/756,568 01/13/04
Seiki Ogura et al.
PROCESS FOR MAKING AND PROGRAMMING
AND OPERATING A DUAL-BIT MULTI-
LEVEL BALLISTIC MONOS MEMORY

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on February 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date SB Ackerman 2/17/04



HALO-99-006BB

Chang et al., "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, pp. 253-255, July 1998, discusses side wall polysilicon gates with MONOS structure.

Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell with Ballistic Direct Injection for EEPROM/Flash", IEDM 1998, p. 987, discusses the improvement of the ballistic injection mechanism.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Doctor Number (Specimen)

Application Number:

HALO-99-006BB

10/756, 568

Applicants

Seiki Ogura et al.

Final Date

01/13/04

Group Art Unit

EXAMINER
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COUNTRY

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Translation

YES

NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

- Chang et al., "A New Nonvolatile Memory Using Source-Side Injection for Programming," IEEE Electron Device Letters, Vol. 19, No. 7, pp. 253-255, July 1998.
- Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell with Ballistic Direct Injection for EEPROM/Flash," IEDM 1998, p. 987

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.